

TSM80N950CP ROG

TSM80N950CP ROG Information

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Part Number TSM80N950CP ROG Manufacturer TSC America Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET, SINGLE, N-CHANNEL, SUPER**Package**TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com



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TSM80N950CP ROG Specifications

Manufacturer Part Number TSM80N950CP ROG Manufacturer TSC America Inc. Category Discrete Semiconductor Products Ferror Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 800V Current - Continuous Drain (Id) @ 25°C 6A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 19.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 691pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 110W (Tc) Rds On (Max) @ Id, Vgs 950 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		
Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Parin to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 6A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 19.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 691pF @ 100V Vgs (Max) ### 30V ### 3	Manufacturer Part Number	TSM80N950CP ROG
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs19.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds691pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs950 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs19.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds691pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs950 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	-
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature For Surface Mount Supplier Device Package Package / Case FA (Tc) 6A	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs19.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds691pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs950 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	800V
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Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 691pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 950 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 950 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)110W (Tc)Rds On (Max) @ Id, Vgs950 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	19.6nC @ 10V
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Rds On (Max) @ Id, Vgs950 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	110W (Tc)
Mounting Type Surface Mount TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	950 mOhm @ 3A, 10V
Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	TO-252, (D-Pak)
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
A. Carrier and Car		Report errors?

TSM80N950CP ROG Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

TSM80N950CP ROG Payment Methods



















TSM80N950CP ROG Shipping Methods













If you have any question about TSM80N950CP ROG, please do not hesitate to contact us!

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